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Will Conley
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Contents

Part One

xvii *Conference Committee*

SESSION 1 INVITED SESSION

7640 03 **Shaping the future of nanoelectronics beyond the Si roadmap with new materials and devices (Invited Paper)** [7640-02]
M. Heyns, F. Bellenger, IMEC (Belgium) and Katholieke Univ. Leuven (Belgium); G. Brammertz, M. Caymax, M. Cantoro, S. De Gendt, B. De Jaeger, A. Delabie, IMEC (Belgium); G. Eneman, IMEC (Belgium), Katholieke Univ. Leuven (Belgium), and FWO-Vlaanderen (Belgium); G. Groeseneken, G. Hellings, M. Houssa, IMEC (Belgium) and Katholieke Univ. Leuven (Belgium); F. Iacopi, D. Leonelli, D. Lin, W. Magnus, IMEC (Belgium); K. Martens, IMEC (Belgium), Katholieke Univ. Leuven (Belgium), and FWO-Vlaanderen (Belgium); C. Merckling, M. Meuris, J. Mitard, J. Penaud, G. Pourtois, M. Scarrozza, E. R. Simoen, B. Soree, S. Van Elshocht, IMEC (Belgium); W. Vandenberghe, IMEC (Belgium) and Katholieke Univ. Leuven (Belgium); A. Vandooren, P. Vereecke, A. Verhulst, W.-E. Wang, IMEC (Belgium)

SESSION 2 FREEFORM AND SMO

7640 05 **Generation of arbitrary freeform source shapes using advanced illumination systems in high-NA immersion scanners** [7640-04]
J. Zimmermann, P. Gräupner, J. T. Neumann, D. Hellweg, D. Jürgens, M. Patra, C. Hennerkes, M. Maul, Carl Zeiss SMT AG (Germany); B. Geh, Carl Zeiss SMT AG (Germany) and ASML US, Inc. (United States); A. Engelen, O. Noordman, M. Mulder, ASML (Netherlands); S. Park, J. De Vocht, Brion Technologies, Inc. (United States)

7640 06 **Demonstrating the benefits of source-mask optimization and enabling technologies through experiment and simulations** [7640-05]
D. Melville, A. E. Rosenbluth, IBM Thomas J. Watson Research Ctr. (United States); K. Tian, K. Lai, IBM Semiconductor Research and Development Ctr. (United States); S. Bagheri, IBM Thomas J. Watson Research Ctr. (United States); J. Tirapu-Azpiroz, J. Meiring, IBM Semiconductor Research and Development Ctr. (United States); S. Halle, G. McIntyre, IBM Research at Albany Nanotech (United States); T. Faure, IBM Mask House (United States); D. Corliss, A. Krasnoperova, L. Zhuang, IBM Semiconductor Research and Development Ctr. (United States); P. Strenski, A. Waechter, L. Ladanyi, F. Barahona, D. Scarpazza, J. Lee, IBM Thomas J. Watson Research Ctr. (United States); T. Inoue, M. Sakamoto, H. Muta, IBM Research Tokyo (Japan); A. Wagner, IBM Thomas J. Watson Research Ctr. (United States); G. Burr, Y. Kim, IBM Almaden Research Ctr. (United States); E. Gallagher, M. Hibbs, IBM Mask House (United States); A. Tritchkov, Y. Granik, M. Fakhry, K. Adam, G. Berger, M. Lam, A. Dave, N. Cobb, Mentor Graphics Corp. (United States)

7640 07 **Tolerancing analysis of customized illumination for practical applications of source and mask optimization** [7640-06]
T. Matsuyama, N. Kita, T. Nakashima, O. Tanitsu, S. Owa, Nikon Corp. (Japan)

7640 08 **Freeform illumination sources: an experimental study of source-mask optimization for 22-nm SRAM cells** [7640-07]
J. Bekaert, B. Laenens, S. Verhaegen, L. Van Look, D. Trivkovic, F. Lazzarino, G. Vandenberghe, IMEC vzw (Belgium); P. van Adrichem, ASML-BRION (United States) and ASML (Netherlands); R. Socha, S. Baron, M. C. Tsai, K. Ning, S. Hsu, H. Y. Liu, ASML-BRION (United States); M. Mulder, A. Bouma, E. van der Heijden, O. Mouraille, K. Schreel, J. Finders, M. Dusa, ASML (Netherlands); J. Zimmermann, P. Gräupner, J. T. Neumann, C. Hennerkes, Carl Zeiss SMT AG (Germany)

SESSION 3 DOUBLE PATTERNING I

7640 09 **Evaluation of double-patterning techniques for advanced logic nodes** [7640-08]
C. Koay, S. Holmes, K. Petrillo, M. Colburn, S. Burns, IBM Corp. (United States); S. Dunn, Tokyo Electron Technology Ctr., America, LLC (United States); J. Cantone, Tokyo Electron America, Inc. (United States); D. Hetzer, S. Kawakami, Tokyo Electron Technology Ctr., America, LLC (United States); Y. van Dommelen, A. Jiang, M. Many, R. Routh, ASML (United States); L. Huli, B. Martinick, M. Rodgers, Univ. at Albany, SUNY (United States); H. Tomizawa, Toshiba (United States); S. Kini, KLA-Tencor (United States)

7640 0A **Actual performance data analysis of overlay, focus, and dose control of an immersion scanner for double patterning** [7640-09]
S. Wakamoto, Y. Kanaya, J. Kosugi, N. Kasai, H. Nishinaga, K. Shiraishi, Y. Shirata, Y. Ishii, Nikon Corp. (Japan)

7640 0B **Modeling of double patterning interactions in litho-cure-litho-etch (LCLE) processes** [7640-10]
A. Erdmann, F. Shao, Fraunhofer Institute for Integrated Systems and Device Technology (Germany); J. Fuhrmann, A. Fiebach, Weierstrass Institute for Applied Analysis and Stochastics (Germany); G. P. Patsis, Institute of Microelectronics (Greece); P. Trefonas, Dow Electronic Materials (United States)

7640 0C **Litho and patterning challenges for memory and logic applications at the 22-nm node** [7640-11]
J. Finders, ASML (Netherlands); M. Dusa, ASML US Inc. (Netherlands); P. Nikolsky, Y. van Dommelen, ASML (Netherlands); R. Watso, ASML Albany (United States); T. Vandeweyer, J. Beckaert, B. Laenens, L. Van Look, IMEC vzw (Belgium)

7640 0D **Comparative study of resolution limits for double patterning and EUV processes for the 32-nm contact hole case** [7640-12]
I. Kamohara, K. Tajima, Nihon Synopsys GK (Japan); T. Schmoeller, Synopsys GmbH (Germany)

SESSION 4 DOUBLE PATTERNING II

7640 0E **Advances in dual-tone development for pitch frequency doubling** [7640-13]
C. Fonseca, M. Somervell, S. Scheer, Tokyo Electron America, Inc. (United States); Y. Kuwahara, K. Nafus, Tokyo Electron Kyushu Ltd. (Japan); R. Gronheid, IMEC (Belgium); S. Tarutani, Y. Enomoto, FUJIFILM Corp. (Japan)

7640 0F **Spacer defined double patterning for sub-72-nm pitch logic technology** [7640-14]
R. Kim, GLOBALFOUNDRIES Inc. (United States); E. Mclellan, Y. Yin, J. Arnold, S. Kanakasabapathy, S. Mehta, IBM Research (United States); Y. Ma, GLOBALFOUNDRIES Inc. (United States); M. Burkhardt, IBM Research (United States); J. Cain, GLOBALFOUNDRIES Inc. (United States); G. McIntyre, M. E. Colburn, IBM Research (United States); H. J. Levinson, GLOBALFOUNDRIES Inc. (United States)

7640 0G **The impact of optical non-idealities in litho-litho-etch processing** [7640-15]
S. A. Robertson, KLA-Tencor Corp. (United States); M. T. Reilly, DOW Electronic Materials (United States); T. Graves, M. D. Smith, J. J. Biafore, KLA-Tencor Corp. (United States)

7640 0H **Double patterning lithography study with high overlay accuracy** [7640-16]
T. Kikuchi, Y. Shirata, M. Yasuda, Y. Iriuchijima, K. Takemasa, R. Tanaka, A. Hazelton, Y. Ishii, Nikon Corp. (Japan)

7640 0I **Litho-process-litho for 2D 32-nm hp Logic and DRAM double patterning** [7640-17]
P. Wong, V. Wiaux, S. Verhaegen, N. Vandenbroeck, IMEC (Belgium)

7640 0J **Modeling of exploration of reversible contrast enhancement layers for double exposure lithography** [7640-18]
F. Shao, Fraunhofer Institute for Integrated Systems and Device Technology (Germany); G. D. Cooper, Z. Chen, Pixelligent Technologies LLC (United States); A. Erdmann, Fraunhofer Institute for Integrated Systems and Device Technology (Germany)

SESSION 5 COMPUTATIONAL LITHOGRAPHY

7640 0K **Improving aberration control with application specific optimization using computational lithography** [7640-19]
J. Zhou, Micron Technology, Inc. (United States); Y. Zhang, Brion Technologies (United States); P. Engblom, ASML (United States); M. Hyatt, Micron Technology, Inc. (United States); E. Wu, M. Snajdr, Brion Technologies (United States); A. deVilliers, Y. He, C. Hickman, Micron Technology, Inc. (United States); P. Liu, Brion Technologies (United States); D. de Lang, ASML Netherlands B.V. (Netherlands); B. Geh, Carl Zeiss SMT (United States); E. Byers, S. Light, Micron Technology, Inc. (United States)

7640 0L **Evaluation of lithographic benefits of using ILT techniques for 22 nm-node** [7640-20]
Y. Zou, Y. Deng, J. Kye, L. Capodieci, C. Tabery, GLOBALFOUNDRIES Inc. (United States); T. Dam, A. Aadamov, K.-H. Baik, L. Pang, B. Gleason, Luminescent Technologies, Inc. (United States)

7640 0M **A computational method for optimal application specific lens control in microlithography** [7640-21]
P. Liu, M. Snajdr, Z. Zhang, Y. Cao, J. Ye, Y. Zhang, Brion Technologies, Inc. (United States)

7640 0N **Aerial image calculation by eigenvalues and eigenfunctions of a matrix that includes source, pupil, and mask** [7640-22]
K. Yamazoe, A. R. Neureuther, Univ. of California, Berkeley (United States)

7640 0O **Optimization from design rules, source and mask, to full chip with a single computational lithography framework: level-set-methods-based inverse lithography technology (ILT)** [7640-23]
L. Pang, D. Peng, P. Hu, D. Chen, T. Cecil, L. He, G. Xiao, V. Tolani, T. Dam, K.-H. Baik, B. Gleason, Luminescent Technologies, Inc. (United States)

7640 0P **Quadratic blur kernels for latent image formation modeling** [7640-24]
A. Burov, Shanghai Microelectronics Equipment Corp. (China)

SESSION 6 POLARIZATION

7640 0Q **In-situ Mueller matrix polarimetry of projection lenses for 193-nm lithography** [7640-25]
H. Nomura, I. Higashikawa, Toshiba Corp. (Japan)

7640 0R **Experimental result of polarization characteristics separation method** [7640-26]
T. Fujii, K. Suzuki, J. Kogo, K. Toyama, K. Sasada, Nikon Corp. (Japan); M. Sawada, Nikon Systems Inc. (Japan)

SESSION 7 BEYOND 22 NM

7640 0S **Implementing and validating double patterning in 22-nm to 16-nm product design and patterning flows** [7640-27]
M.-S. Noh, B.-S. Seo, S.-J. Lee, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); A. Miloslavsky, Synopsys (United States); C. Cork, Synopsys SARL (France); L. Barnes, Synopsys Technology Park (United States); K. Lucas, Synopsys Inc. (United States)

7640 0T **Comparative study of line width roughness (LWR) in next-generation lithography (NGL) processes** [7640-28]
K. Patel, SanDisk (United States) and Univ. of California, Berkeley (United States); T. Wallow, H. J. Levinson, GLOBALFOUNDRIES Inc. (United States); C. J. Spanos, Univ. of California, Berkeley (United States)

SESSION 8 TOOLS AND PROCESS RESOLUTION EXTENSIONS I

7640 0U **Toward perfect on-wafer pattern placement: stitched overlay exposure tool characterization** [7640-29]
C. P. Ausschnitt, T. A. Brunner, N. M. Felix, IBM SRDC (United States); B. Minghetti, STMicroelectronics (France)

7640 0V **Impact of scanner signatures on optical proximity correction** [7640-30]
J. K. Tyminski, Nikon Precision Inc. (United States); T. Matsuyama, Nikon Corp. (Japan); Y.-L. Lu, J.-C. Lai, K.-T. Chen, Y.-C. Mai, Powerchip Semiconductor Corp. (Taiwan); I. Su, Nikon (Japan); G. Bailey, Synopsys Taiwan Ltd. (Taiwan)

7640 0W **Overlay characterization and matching of immersion photoclusters** [7640-31]
B. Minghetti, STMicroelectronics (United States); T. Brunner, C. Robinson, C. Ausschnitt, D. Corliss, N. Felix, IBM SRDC (United States)

7640 0X **Topcoat-less resist approach for high volume production and yield enhancement of immersion lithography** [7640-32]
K. Nakano, R. Seki, T. Kawakubo, Y. Maruta, T. Sekito, K. Shiraishi, T. Sei, T. Fujiwara, T. Hayashi, Y. Iriuchijima, S. Owa, Nikon Corp. (Japan)

7640 0Y **Analysis of the impact of pupil shape variation by pupil fit modeling** [7640-33]
J. Jeon, C. Park, H. Yang, C. Kim, J. Choi, S. Oh, D. Yim, S. Park, Hynix Semiconductor Inc. (Korea, Republic of); K. Park, Y. Min, ASML Korea (Korea, Republic of); A. Engelen, B. Smeets, ASML Netherlands B.V. (Netherlands); J. Zimmermann, Carl Zeiss SMT AG (Germany)

SESSION 9 TOOLS AND PROCESS RESOLUTION EXTENSIONS II

7640 0Z **Predicting and reducing substrate induced focus error** [7640-34]
B. Liegl, B. Sapp, K. Low, S. Greco, T. Brunner, N. Felix, I. Stobert, K. Nafisi, IBM Corp. (United States); C. Sarma, Infineon Technologies (United States)

7640 10 **Lithographic scanner stability improvements through advanced metrology and control** [7640-35]
P. Vanoppen, T. Theeuwes, H. Megens, H. Cramer, T. Fliervoet, M. Ebert, D. Satriasaputra, ASML (Netherlands)

7640 11 **Printing the metal and contact layers for the 32- and 22-nm node: comparing positive and negative tone development process** [7640-69]
L. Van Look, J. Bekaert, V. Truffert, V. Wiaux, F. Lazzarino, M. Maenhoudt, G. Vandenberghe, IMEC (Belgium); M. Reybrouck, FUJIFILM Electronic Materials (Japan); S. Tarutani, FUJIFILM Corp. (Japan)

7640 13 **The impacts of scanner modeling parameters for OPC model of sub-40-nm memory device** [7640-116]
C. Kim, J. Jang, J. Jeon, C. Park, H. Yang, D. Yim, S. Park, Hynix Semiconductor Inc. (Korea, Republic of)

7640 14 **Simulation-based pattern matching using scanner metrology and design data to reduce reliance on CD metrology** [7640-38]
Y. He, E. Byers, S. Light, D. Hines, A. Devilliers, M. Hyatt, J. Zhou, V. Nair, Micron Technology, Inc. (United States); Z. Yu, Y. Cao, X. Xie, W. Shao, R. Aldana, R. Goossens, C.-Q. Ma, J. Lu, H. Liu, C. Aquino, Brion Technologies, Inc. (United States); P. Engblom, T. Nooitgedagt, E. Janda, ASML (United States)

7640 15 **The GridMapper challenge: how to integrate into manufacturing for reduced overlay error** [7640-39]
A. Gabor, B. Liegl, M. Pike, E. Hwang, T. Wiltshire, IBM Systems and Technology Group (United States)

7640 16 **Simultaneous optimization of dose and focus controls in advanced ArF immersion scanners** [7640-40]
T. Toki, Nikon Corp. (Japan); P. Izikson, KLA-Tencor Corp. Israel (Israel); J. Kosugi, N. Sakasai, K. Saotome, K. Suzuki, Nikon Corp. (Japan); D. Kandel, KLA-Tencor Corp. Israel (Israel); J. C. Robinson, KLA-Tencor Corp. (United States); Y. Koyanagi, KLA-Tencor Japan (Japan)

SESSION 10 MASK, LAYOUT, AND OPC

7640 17 **Novel fine-tuned model-based SRAF generation method using coherence map** [7640-41]
K. Kodera, S. Tanaka, M. Yamaji, Toshiba Corp. (Japan); C. Kodama, Toshiba Memory Systems Co., Ltd. (Japan); T. Kotani, S. Nojima, K. Hashimoto, S. Mimotogi, S. Inoue, Toshiba Corp. (Japan)

7640 18 **Ultimately accurate SRAF replacement for practical phases using an adaptive search algorithm based on the optimal gradient method** [7640-42]
S. Maeda, Toshiba Corp. (Japan); H. Nosato, National Institute of Advanced Industrial Science and Technology (Japan); T. Matsunawa, M. Miyairi, S. Nojima, S. Tanaka, Toshiba Corp. (Japan); H. Sakanashi, M. Murakawa, National Institute of Advanced Industrial Science and Technology (Japan); T. Saito, Toshiba Microelectronics Corp. (Japan); T. Higuchi, National Institute of Advanced Industrial Science and Technology (Japan); S. Inoue, Toshiba Corp. (Japan)

7640 19 **22-nm logic lithography in the presence of local interconnect** [7640-43]
M. C. Smayling, Tela Innovations, Inc. (United States); R. J. Socha, M. V. Dusa, ASML (United States)

7640 1A **Lithography and layout co-optimization beyond conventional OPC concept** [7640-44]
K. Tsujita, K. Mikami, H. Ishii, T. Arai, K. Takahashi, Canon Inc. (Japan)

7640 1B **Mask enhancer technology for sub-100-nm pitch random logic layout contact hole fabrication** [7640-45]
T. Yuito, H. Sakaue, T. Matsuda, T. Shimizu, S. Irie, F. Iwamoto, A. Misaka, T. Koizumi, M. Sasago, Semiconductor Co., Panasonic Corp. (Japan)

7640 1C **Suppressing ringing effects from very strong off-axis illumination with novel OPC approaches for low k1 lithography** [7640-46]
C. Cork, Synopsys SARL (France); F. Amoroso, A. Poonawala, S. Jang, K. Lucas, Synopsys Inc. (United States)

SESSION 11 MODELING

7640 1D **Three-dimensional physical photoresist model calibration and profile-based pattern verification** [7640-47]
M. Talbi, A. Y. Abdo, T. C. Bailey, IBM Corp. (United States); W. Conley, Freescale Semiconductor, Inc. (United States); D. N. Dunn, IBM Corp. (United States); M. Fujimoto, NEC Electronics (United States); J. Nickel, IBM Corp. (United States); N. Y. Chung, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); S. Marokkey, Infineon Technologies (United States); S. H. Lee, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); C. Sarma, Infineon Technologies (United States); D. Shao, R. Viswanathan, IBM Corp. (United States)

7640 1E **The feasibility of using image parameters for test pattern selection during OPC model calibration** [7640-48]
A. Abdo, R. Viswanathan, IBM Systems and Technology Group (United States)

7640 1F **Optical proximity correction enhancement by using model based fragmentation approaches** [7640-49]
Y.–S.Woo, W.-H. Choi, B.-S. Seo, Y. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); V. Liubich, S. Abdelwahed, J. Kim, J. Word, Mentor Graphics Corp. (United States); J.-W. Lee, Mentor Graphics Korea (Korea, Republic of)

7640 1G **Automation of sample plan creation for process model calibration** [7640-50]
J. Oberschmidt, IBM Microelectronics (India); A. Abdo, IBM Microelectronics (United States); T. Desouky, M. Al-Imam, Mentor Graphics Corp. (Egypt); A. Krasnoperova, R. Viswanathan, IBM Microelectronics (United States)

SESSION 12 SOURCE-MASK OPTIMIZATION

7640 1H **SMO for 28-nm logic device and beyond: impact of source and mask complexity on lithography performance** [7640-51]
S. Nagahara, K. Yoshimochi, H. Yamazaki, K. Takeda, T. Uchiyama, NEC Electronics Corp. (Japan); S. Hsu, Z. Li, H. Liu, K. Gronlund, T. Kurosawa, J. Ye, L. Chen, H. Chen, Z. Li, X. Liu, W. Liu, ASML Brion Technologies, Inc. (United States)

7640 1I **Illumination optics for source-mask optimization** [7640-52]
Y. Mizuno, T. Matsuyama, S. Owa, O. Tanitsu, N. Kita, M. Okumura, Nikon Corp. (Japan)

7640 1J **Considerations in source-mask optimization for logic applications** [7640-53]
Y. Deng, Y. Zou, K. Yoshimoto, Y. Ma, C. E. Tabery, J. Kye, L. Capodieci, H. J. Levinson, GLOBALFOUNDRIES Inc. (United States)

7640 1K **Challenges for low-k1 lithography in logic devices by source mask co-optimization** [7640-54]
K. Yoshimochi, S. Nagahara, K. Takeda, T. Uchiyama, NEC Electronics Corp. (Japan)

7640 1L **A GPU-based full-chip source-mask optimization solution** [7640-55]
I. Torunoglu, E. Elsen, A. Karakas, Gauda Inc. (United States)

7640 1M **Source mask optimization for advanced lithography nodes** [7640-56]
A. Poonawala, W. Stanton, C. Sawh, Synopsys, Inc. (United States)

Part Two

SESSION 13 TOOLS

7640 1N **Towards ultimate optical lithography with NXT:1950i dual stage immersion platform** [7640-57]
T. Castenmiller, F. van de Mast, T. de Kort, C. van de Vin, M. de Wit, R. Stegen, S. van Cleef, ASML Netherlands B.V. (Netherlands)

7640 1O **Latest performance of immersion scanner S620D with the Streamlign platform for the double patterning generation** [7640-58]
H. Kohno, Y. Shibazaki, J. Ishikawa, J. Kosugi, Y. Iriuchijima, M. Hamatani, Nikon Corp. (Japan)

7640 1P **Performance of FlexRay: a fully programmable illumination system for generation of freeform sources on high NA immersion systems** [7640-59]
M. Mulder, A. Engelen, O. Noordman, G. Streutker, B. van Drieenhuizen, C. van Nuenen, W. Endendijk, J. Verbeeck, W. Bouman, A. Bouma, R. Kazinczi, ASML (Netherlands); R. Socha, ASML Brion Technologies Inc. (United States); D. Jürgens, J. Zimmermann, B. Trauter, Carl Zeiss SMT AG (Germany); J. Bekaert, B. Laenens, IMEC vzw (Belgium); D. Corliss, G. McIntyre, IBM Microelectronics (United States)

7640 1Q **High reliability ArF light source for double patterning immersion lithography** [7640-60]
R. Rokitski, T. Ishihara, R. Rao, R. Jiang, M. Haviland, T. Cacouris, D. Brown, Cymer, Inc. (United States)

7640 1R **Advanced imaging with 1.35 NA immersion systems for volume production** [7640-61]
I. Bouchoms, J. Mulkens, S. de Putter, P. Gunter, R. de Graaf, M. Beems, E. Verdurmen, H. Jasper, ASML Netherlands B.V. (Netherlands); N. Dieckmann, Carl Zeiss SMT AG (Germany); F. Bornebroek, ASML Netherlands B.V. (Netherlands)

POSTER SESSION: COMPUTATIONAL LITHOGRAPHY

7640 1S **The impact of resist model on mask 3D simulation accuracy beyond 40-nm node memory patterns** [7640-62]
K.-T. Chen, S.-S. Yeh, Y.-H. Hsieh, J.-C. N. Lai, Powerchip Semiconductor Corp. (Taiwan); S. A. Robertson, J. J. Biafore, S. Kapasi, A. Lin, KLA-Tencor Corp. (United States)

7640 1T **Comparison of OPC models with and without 3D-mask effect** [7640-63]
J.-H. Ser, T.-H. Park, M.-G. Jeong, E.-M. Lee, S.-W. Lee, C.-S. Suh, S.-W. Choi, C.-H. Park, J.-T. Moon, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)

7640 1U **Virtual fab flow for wafer topography aware OPC** [7640-64]
H.-J. Stock, Synopsys GmbH (Germany); L. Bomholt, Synopsys Switzerland LLC (Switzerland); D. Krüger, Synopsys GmbH (Germany); J. Shiely, H. Song, Synopsys Inc. (United States); N. Voznesenskiy, Riia (Estonia)

7640 1V **Interlayer self-aligning process for 22-nm logic** [7640-66]
M. C. Smayling, Tela Innovations, Inc. (United States); S. Robertson, KLA-Tencor (United States); D. Lacey, Cavendish Kinetics, Inc. (United States); S. Kapasi, KLA-Tencor (United States)

7640 1W **Process window and integration results for full-chip model-based assist-feature placement at the 32-nm node and below** [7640-67]
J. Li, Synopsys, Inc. (China); G. Luk-Pat, A. Poonawala, K. Lucas, B. Painter, Synopsys, Inc. (United States)

7640 1X **The role of mask topography effects in the optimization of pixelated sources** [7640-68]
V. Domnenko, Synopsys, Inc. (Russian Federation); B. Küchler, T. Mülders, T. Schmöller, H.-J. Stock, G. Viehöver, Synopsys, Inc. (Germany)

POSTER SESSION: DOUBLE PATTERNING

7640 1Y **Experimental study of effect of pellicle on optical proximity fingerprint for 1.35 NA immersion ArF lithography** [7640-36]
L. Van Look, J. Bekaert, B. Laenens, G. Vandenberghe, IMEC (Belgium); J. Richter, K. Bubke, J. H. Peters, Advanced Mask Technology Ctr. GmbH (Germany); K. Schreel, M. Dusa, ASML B.V. (Netherlands)

7640 1Z **Achieving interferometric double patterning through wafer rotation** [7640-70]
P. Xie, N. V. Lafferty, B. W. Smith, Rochester Institute of Technology (United States)

7640 20 **Novel ATHENA mark design to enhance alignment quality in double patterning with spacer process** [7640-71]
L. W. Chen, M. Yang, E. Yang, T. H. Yang, K. C. Chen, C.-Y. Lu, Macronix International Co., Ltd. (Taiwan)

7640 21 **Modeling of CD and placement error in multi-spacer patterning technology** [7640-72]
S. Babin, K. Bay, aBeam Technologies, Inc. (United States)

7640 22 **LENS (lithography enhancement toward nano scale): a European project to support double exposure and double patterning technology development** [7640-73]
P. Cantu, L. Baldi, P. Piacentini, Numonyx (Italy); J. Sytsma, ASML Netherlands (Netherlands); B. Le Gratiet, STMicroelectronics (France); S. Gaugiran, CEA-LETI (France); P. Wong, IMEC (Belgium); H. Miyashita, Dai Nippon Photomask Europe (Italy); L. R. Atzei, Lam Research Srl (Italy); X. Buch, JSR (Belgium); D. Verkleij, FEI (Netherlands); O. Toublan, Mentor Graphics (France); F. Perez-Murano, Ctr. Nacional de Microelectrónica (Spain); D. Mecerreyes, CIDETEC (Spain)

7640 23 **Self-aligned double patterning process for 32/32-nm contact/space and beyond using 193 immersion lithography** [7640-129]
B. Mebarki, L. Miao, Y. Chen, J. Yu, P. Blanco, J. Makeeff, J. Shu, C. Bencher, M. Naik, C. S. W. Ngai, Applied Materials, Inc. (United States)

POSTER SESSION: FREEFORM AND SMO

7640 24 **Novel continuously shaped diffractive optical elements enable high efficiency beam shaping** [7640-74]
Y. V. Miklyaev, W. Imgrunt, LIMO Lissotschenko Mikrooptik GmbH (Germany); V. S. Pavelyev, Image Processing Systems Institute (Russian Federation); D. G. Kachalov, Samara State Aerospace Univ. (Russian Federation); T. Bizjak, L. Aschke, V. N. Lissotschenko, LIMO Lissotschenko Mikrooptik GmbH (Germany)

7640 25 **Advances in DOE modeling and optical performance for SMO applications** [7640-75]
J. Carriere, J. Stack, J. Childers, K. Welch, M. D. Himel, Tessera (United States)

7640 26 **Abbe-PCA-SMO: microlithography source and mask optimization based on Abbe-PCA** [7640-76]
J. H.-C. Chang, C.-P. C. Chen, National Taiwan Univ. (Taiwan); L. S. Melvin III, Synopsys (United States)

7640 27 **Optimization on illumination source with design of experiments** [7640-77]
H. Hu, Y. Zou, Y. Deng, GLOBALFOUNDRIES Inc. (United States)

7640 28 **Source-mask optimization (SMO): from theory to practice** [7640-78]
T. Dam, V. Tolani, P. Hu, K.-H. Baik, L. Pang, B. Gleason, Luminescent Technologies, Inc. (United States); S. D. Slonaker, J. K. Tyminski, Nikon Precision Inc. (United States)

POSTER SESSION: LASER

7640 29 **Partial spatial coherence in an excimer-laser lithographic imaging system** [7640-79]
A. Smith, A. Burvall, C. Dainty, National Univ. of Ireland, Galway (Ireland)

7640 2A **Flexible and reliable high power injection locked laser for double exposure and double patterning ArF immersion lithography** [7640-80]
M. Yoshino, H. Umeda, H. Tsushima, H. Watanabe, S. Tanaka, S. Matsumoto, T. Onose, H. Nogawa, Y. Kawasuji, T. Matsunaga, J. Fujimoto, H. Mizoguchi, Gigaphoton Inc. (Japan)

7640 2B **Laser bandwidth effect on overlay budget and imaging for the 45-nm and 32-nm technology nodes with immersion lithography** [7640-81]
U. Iessi, Numonyx (Italy); M. Kupers, Cymer B.V. (Netherlands); E. De Chiara, P. Rigolli, Numonyx (Italy); I. Lalovic, Cymer, Inc. (United States); G. Capetti, Numonyx (Italy)

7640 2C **Laser spectrum requirements for tight CD control at advanced logic technology nodes** [7640-83]
R. C. Peng, H. J. Lee, J. Lin, Taiwan Semiconductor Manufacturing Corp. (Taiwan); A. Lin, KLA-Tencor Corp. (Taiwan); A. Chang, B. S.-M. Lin, Cymer Inc. (Taiwan)

7640 2D **Lithography light source fault detection** [7640-125]
M. Graham, E. Pantel, P. Nelissen, J. Moen, E. Tincu, W. Dunstan, D. Brown, Cymer, Inc. (United States)

POSTER SESSION: LITHOGRAPHY OPTIMIZATION

7640 2E **Pattern deformation caused by deformed pellicle with ArF exposure** [7640-85]
J.-H. You, Hanyang Univ. (Korea, Republic of); I. An, Nano-View Co. (Korea, Republic of); H.-K. Oh, Hanyang Univ. (Korea, Republic of)

7640 2I **Study for lithography techniques of hybrid mask shape of contact hole with 1.35-NA polarized illumination for 28-nm-node and below logic LSI** [7640-88]
Y. Setta, K. Kobayashi, T. Chijimatsu, S. Asai, Fujitsu Microelectronics Ltd. (Japan)

POSTER SESSION: MASK LAYOUT AND OPC

7640 2J **Applications of MoSi-based binary intensity mask for sub-40-nm DRAM** [7640-89]
T.-S. Eom, E.-K. Shin, E.-H. Lee, Y.-J. Ryu, J.-T. Park, S. Koo, H.-J. Shin, S.-H. Hwang, H.-Y. Lim, S. Park, K.-T. Sun, N.-J. Kwak, S. Park, Hynix Semiconductor Inc. (Korea, Republic of)

7640 2K **OMOG mask topography effect on lithography modeling of 32-nm contact hole patterning** [7640-90]
L. Yuan, W. Zhou, GLOBALFOUNDRIES Singapore (Singapore); L. L. Zhuang, IBM Microelectronics (United States); K. S. Yoon, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); Q. Y. Lin, GLOBALFOUNDRIES Singapore (Singapore); S. Mansfield, IBM Microelectronics (United States)

7640 2L **Fast-converging iterative gradient decent methods for high pattern fidelity inverse mask design** [7640-91]
J.-C. Yu, P. Yu, National Chiao Tung Univ. (Taiwan)

7640 2M **Radial segmentation approach for contact hole patterning in 193-nm immersion lithography** [7640-92]
M. L. Ling, National Univ. of Singapore (Singapore); G. S. Chua, S. K. Tan, GLOBALFOUNDRIES Singapore (Singapore); C. J. Tay, C. Quan, National Univ. of Singapore (Singapore); Q. Lin, GLOBALFOUNDRIES Singapore (Singapore)

7640 2N **Binary mask optimization for forward lithography based on boundary layer model in coherent systems** [7640-93]
X. Ma, G. R. Arce, Univ. of Delaware (United States)

7640 2O **Improvement in process window aware OPC** [7640-94]
X. Li, Synopsys Inc. (United States); Y. Kojima, H. Taoka, A. Moniwa, Renesas Technology Co. (Japan); M. St. John, Y. Ping, R. Brown, R. Lugg, S. Lee, Synopsys Inc. (United States)

7640 2P **A non-delta-chrome OPC methodology for process models with three-dimensional mask effects** [7640-95]
P. C. W. Ng, K.-Y. Tsai, National Taiwan Univ. (Taiwan); C.-H. Tang, National Taiwan Univ. (Taiwan) and Synopsys Taiwan Ltd. (Taiwan); L. Melvin, Synopsys, Inc. (United States)

7640 2Q **A new etch-aware after development inspection (ADI) technique for OPC modeling** [7640-96]
J. Xue, J. Huang, A. Kazarian, B. Falch, Synopsys, Inc. (United States)

7640 2S **Wafer LMC accuracy improvement by adding mask model** [7640-98]
W. C. Lo, Y. F. Cheng, M. J. Chen, P. Haung, United Microelectronics Corp. (Taiwan); S. Chang, Brion Technologies (United States); E. Tsujimoto, Dai Nippon Printing Co. (Japan)

7640 2T **Study of model based etch bias retarget for OPC** [7640-99]
Q. Liu, R. Cheng, Semiconductor Manufacturing International Corp. (China); L. Zhang, Mentor Graphics Corp. (China)

7640 2U **Intra field CD uniformity correction by Scanner Dose Mapper using Galileo mask transmission mapping as the CDU data source** [7640-126]
G. S. Chua, GLOBALFOUNDRIES Singapore (Singapore); C. Eran, Carl Zeiss SMS (Israel); S. K. Tan, B. I. Choi, T. H. Ng, P. L. Lua, GLOBALFOUNDRIES Singapore (Singapore); O. Sharoni, G. Ben-Zvi, Carl Zeiss SMS (Israel)

POSTER SESSION: MATERIALS

7640 2W **Metamaterials for enhancement of DUV lithography (Best Student Paper Award)** [7640-101]
A. Estroff, N. V. Lafferty, P. Xie, B. W. Smith, Rochester Institute of Technology (United States)

7640 2Y **Toward a consistent and accurate approach to modeling projection optics** [7640-103]
D. Peng, P. Hu, V. Tolani, T. Dam, Luminescent Technologies (United States); J. Tyminski, S. Slonaker, Nikon Precision Inc. (United States)

7640 2Z **High fluence testing of optical materials for 193-nm lithography extensions applications** [7640-127]
V. Liberman, S. Palmacci, G. P. Geurtsen, M. Rothschild, MIT Lincoln Lab. (United States); P. A. Zimmerman, SEMATECH Inc. (United States)

POSTER SESSION: MODELING

7640 30 **Stepwise fitting methodology for optical proximity correction modeling** [7640-104]
A. Isoyan, J. Li, L. S. Melvin III, Synopsys, Inc. (United States)

7640 31 **Automatic numerical determination of lateral influence functions for fast-CAD** [7640-105]
M. A. Miller, Univ. of California, Berkeley (United States); K. Yamazoe, Univ. of California, Berkeley (United States) and Canon Inc. (Japan); A. R. Neureuther, Univ. of California, Berkeley (United States)

7640 32 **Aerial image model and application to aberration measurement** [7640-106]
A. Y. Bourov, L. Li, Z. Yang, F. Wang, L. Duan, Shanghai Micro Electronics Equipment Co., Ltd. (China)

7640 33 **Methods for benchmarking photolithography simulators: part V** [7640-107]
T. Graves, M. D. Smith, S. H. Kapasi, KLA-Tencor Corp. (United States)

7640 34 **Selective inverse lithography methodology** [7640-108]
C. Lim, V. Temchenko, Infineon Technologies Dresden GmbH and Co. OHG (Germany); M. Niehoff, Mentor Graphics Corp. (Germany)

7640 35 **CDU linear model based on aerial image principal components** [7640-109]
Z. Yang, A. Y. Burov, L. Li, F. Wang, Z. Chu, Shanghai Micro Electronics Equipment Co., Ltd. (China)

7640 36 **Impact of illumination on model-based SRAF placement for contact patterning** [7640-110]
J. L. Sturtevant, S. Jayaram, O. El-Sewefy, A. Dave, P. LaCour, Mentor Graphics Corp. (United States)

7640 37 **A novel decomposition of source kernel for OPC modeling** [7640-111]
C. T. Hsuan, T. S. Wu, F. Lo, E. Yang, T. H. Yang, K. C. Chen, C.-Y. Lu, Macronix International Co., Ltd. (Taiwan)

7640 38 **Methods for assessing empirical model parameters and calibration pattern measurements** [7640-112]
X. Zhou, E. Khaliullin, L. Luan, Luminescent Technologies (United States)

7640 39 **A simplified reaction-diffusion system of chemically amplified resist process modeling for OPC** [7640-113]
Y. Fan, Synopsys, Inc. (United States); M.-G. Jeong, J. Ser, S.-W. Lee, C. Suh, Samsung Electronics (Korea, Republic of); K.-I. Koo, S. Lee, Synopsys, Inc. (Korea, Republic of); I. Su, Synopsys, Inc. (Taiwan); L. Zavyalova, B. Falch, J. Huang, Synopsys, Inc. (United States); T. Schmoeller, Synopsys, Inc. (Germany)

7640 3A **Improved process window modeling techniques** [7640-114]
C. Zuniga, T. Tawfik, Mentor Graphics Corp. (United States)

POSTER SESSION: TOOLS AND PROCESS CONTROL

7640 3B **Lithography cycle time improvements using short-interval scheduling** [7640-115]
D. Norman, S. Watson, M. Anderson, S. Marteney, B. Mehr, Applied Materials, Inc. (United States)

7640 3C **Topography-aware BARC optimization for double patterning** [7640-117]
S. Liu, T. Fühner, F. Shao, Fraunhofer Institute for Integrated Systems and Device Technology (Germany); A. Barenbaum, Fraunhofer Institute for Integrated Systems and Device Technology (Germany) and Univ. of Erlangen-Nuremberg (Germany); J. Jahn, Univ. of Erlangen-Nuremberg (Germany); A. Erdmann, Fraunhofer Institute for Integrated Systems and Device Technology (Germany)

7640 3E **A novel method to reduce wafer topography effect for implant lithography process** [7640-119]
L. Yuan, S. Bae, Y. F. Fu, A. Chen, H. P. Koh, Q. Y. Lin, GLOBALFOUNDRIES Singapore (Singapore)

7640 3F **Immersion BARC for hyper NA applications II** [7640-121]
Y.–C. Huang, K.-L. Chuang, T.-J. Yeh, S. Wu, B. Lin, W.-L. Huang, B.-J. Lu, E. T. Liu, C. C. Yu, United Microelectronics Corp. (Taiwan); C. Lin, J. Y. Yu, G. Prokopowicz, S. R. Kim, S. Wong, G. Barclay, The Dow Chemical Co. (United States)

7640 3G **Methods and challenges to extend existing dry 193-nm medium NA lithography beyond 90 nm** [7640-122]
J. Schneider, A. Greiner, C. Lim, V. Temchenko, F. Braun, D. Kaiser, T. Hauck, I. Meusel, D. Burmeister, S. Loehr, S. Volkland, A. Bauch, H. Kirbach, D. Sarlette, Infineon Technologies Dresden GmbH (Germany); K. Thiede, Canon Deutschland GmbH (Germany)

7640 3H **Examining reflectivity criterion for various ArF lithography** [7640-123]
M.-F. Tsai, C.-C. Lin, W.-C. Chao, C.-T. Wu, J.-C. Lai, Powerchip Semiconductor Corp. (Taiwan)

7640 3I **CD-uniformity for 45-nm NV memory on product-stack** [7640-124]
U. Iessi, B. Colombo, Numonyx (Italy); J. Plauth, ASML Italy srl (Italy); B. Triulzi, E. De Chiara, P. Canestrari, Numonyx (Italy)

7640 3J **Analysis of photoresist edge bead removal using laser light and gas** [7640-128]
V. Chaplick, E. Degenkolb, D. Elliott, K. Harte, R. Millman, Jr., M. Tardif, UVTech Systems, Inc. (United States)

Author Index